



# SLA-SiPM Final Presentation

ESA Contract No. 4000111544/14/NL/SC  
10/December/2015

# Program Overview

# Program Details

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- SLA-SiPM (Scalable Large Area SiPM)
- ESA Contract No. 4000111544/14/NL/SC
- Kickoff: June 2014
- Planned Completion Date: December 2015
- Milestones
  - Progress (MS 1): Upon successful completion of Task 1 and successful TSV Development Review and acceptance of all related deliverables
  - Progress (MS 2): Upon successful completion of Task 2 and successful Qualification Review and acceptance of all related deliverables
  - Final Settlement (MS 3): Upon the Agency's acceptance of all deliverable items due under the Contract and the Contractor's fulfilment of all other contractual obligations including submission of the Contract Closure Documentation

# Goals

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- **Develop a through silicon via (TSV) large area SiPM package**
  - High fill factor in package
  - High fill factor in array
  - High photon detection efficiency (PDE)
  - Magnetic resonance imaging (MRI) compatible
- **Produce a large area SiPM product**
  - Product driven by market requirements
  - Perform qualification and reliability testing
- **Produce an array from the large area SiPM**
  - Perform qualification and reliability testing
- **Validate product with external customers**

# Task Overview

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- **Task 1 - TSV Development**
  - Development of the Through Silicon Via (TSV) Process
- **Task 2 - TSV Qualification & Reliability**
  - Qualification and reliability assessment of a large area SiPM manufactured in a TSV process
- **Task 3 - Array Development**
  - Production of a large area array based on large area SiPM
- **Task 4 - Program Management**
  - All program management
  - TN1, TN2, TN3, TN4, Final Presentation (this document)

# History of SiPM Development with ESA

Products

SPM Matrix Product  
M-Series (NonP)

B-Series Product  
(PonN)

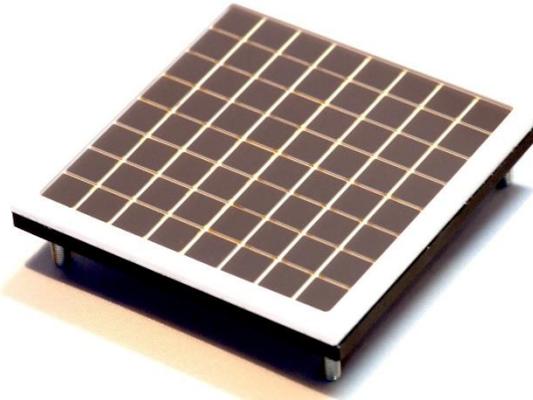


J-Series 6 mm

ESA Programs



DESSA1 & DESSA2



ESSA & TQSPM

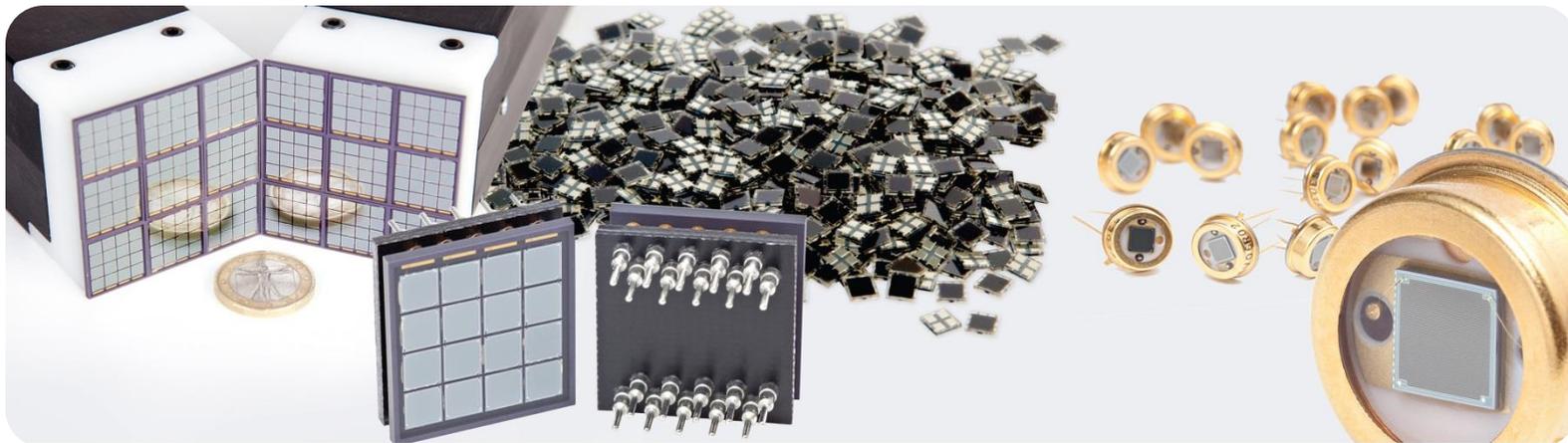


# Background

# SensL Quick Facts

<b>Business</b>	Low Light Sensors
<b>Markets</b>	Medical Imaging Radiation Detection (H&T) Automotive 3D Ranging and Sensing High Energy Physics
<b>Model</b>	Fabless Semiconductor

- Established 2004
- ISO9001:2008 Certified



# SensL Advantages

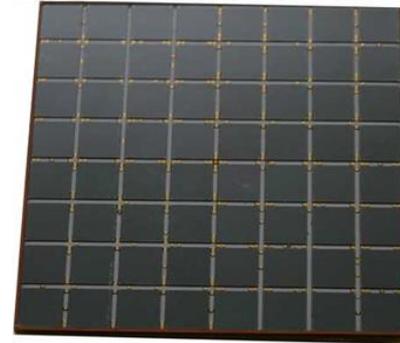
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Photomultiplier  
Vacuum Tube

## SensL Advantages:

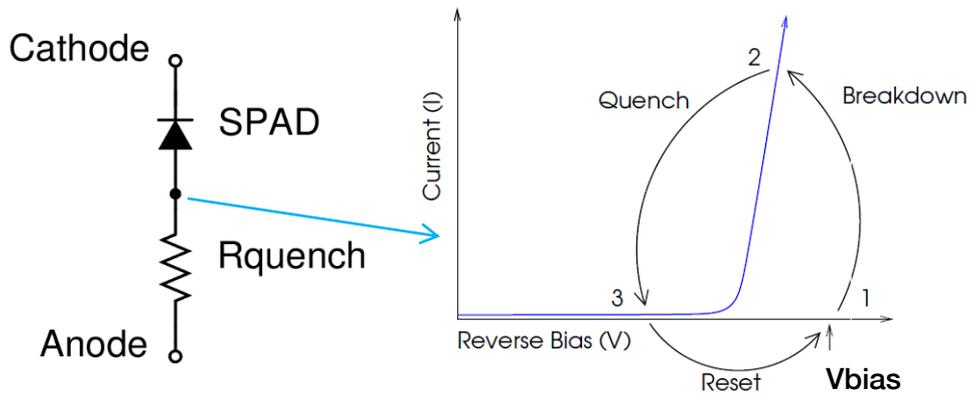
Performance  
Uniformity  
Large Area  
Form Factor  
Low Cost



SensL  
Silicon Photomultiplier



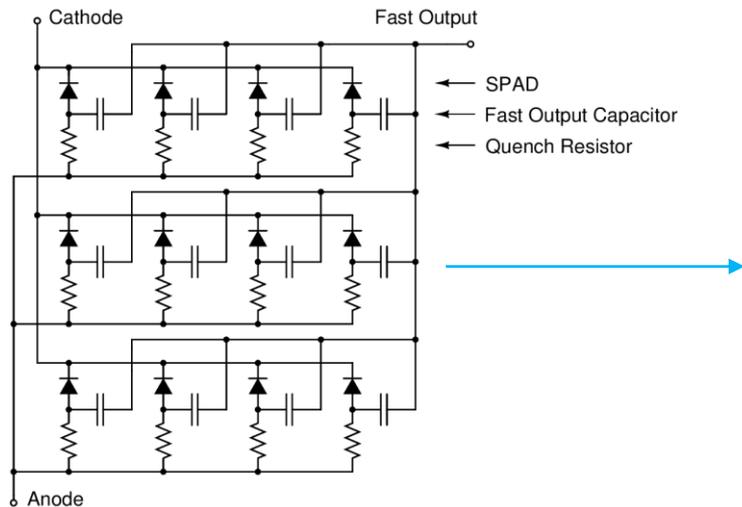
# Overview of SPAD and SiPM Sensors



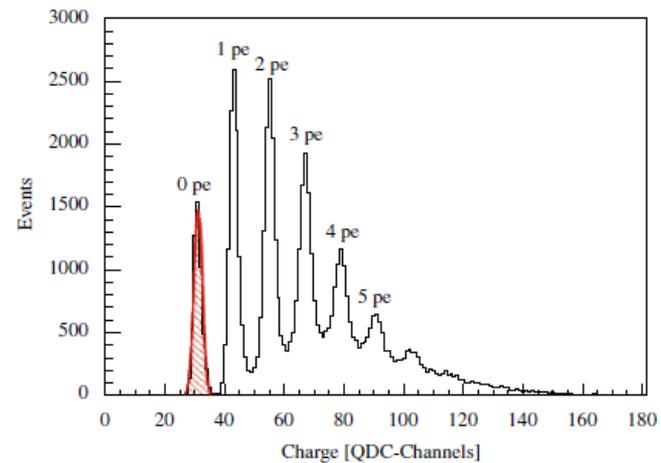
Time or count single photons



SPAD



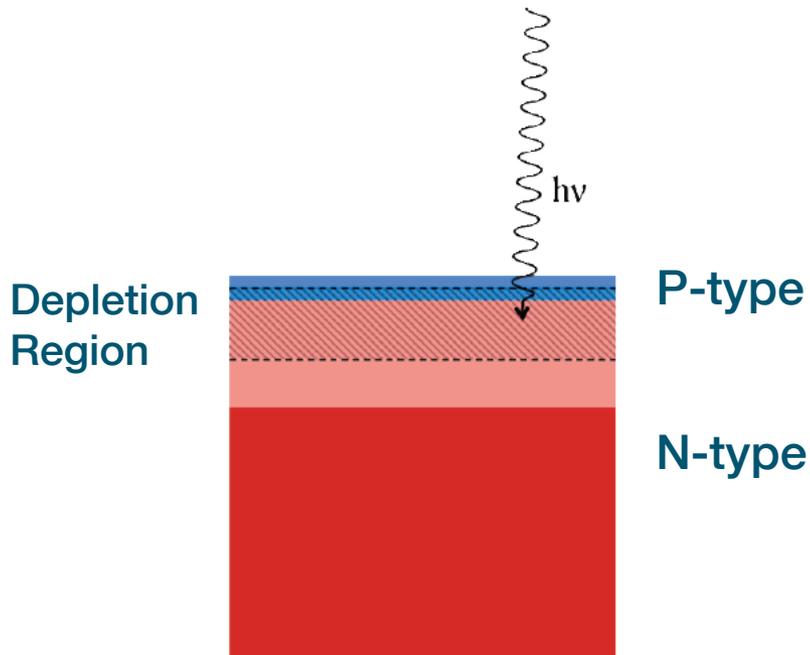
Time or count multiple photons



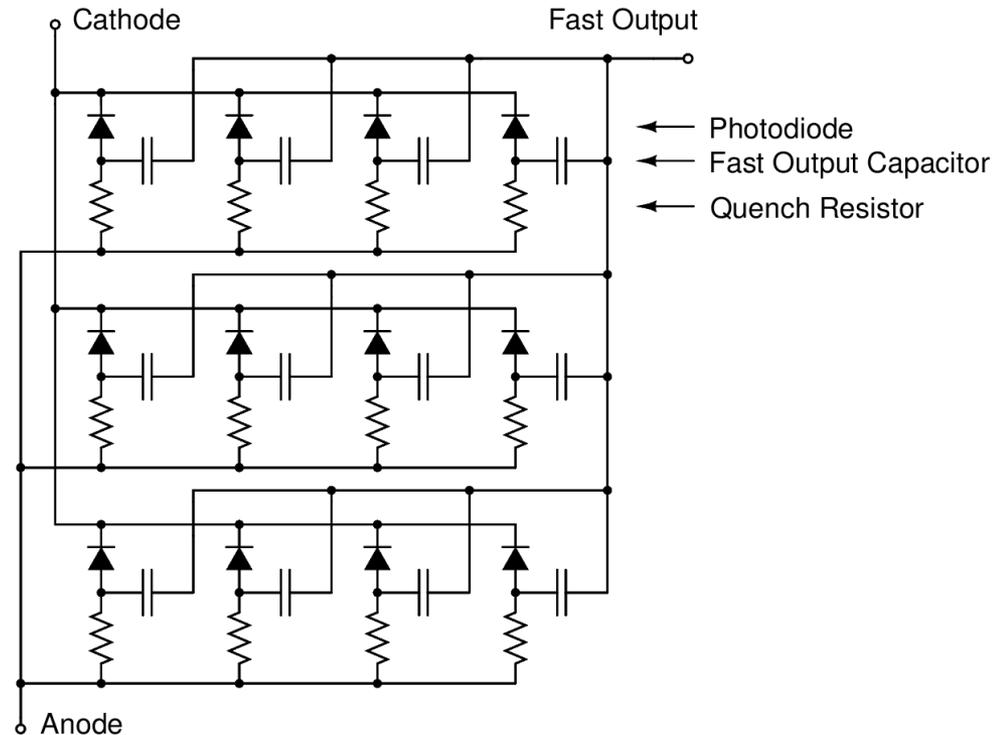
SiPM

# SiPM Technology

## B-Series, C-Series & J-Series



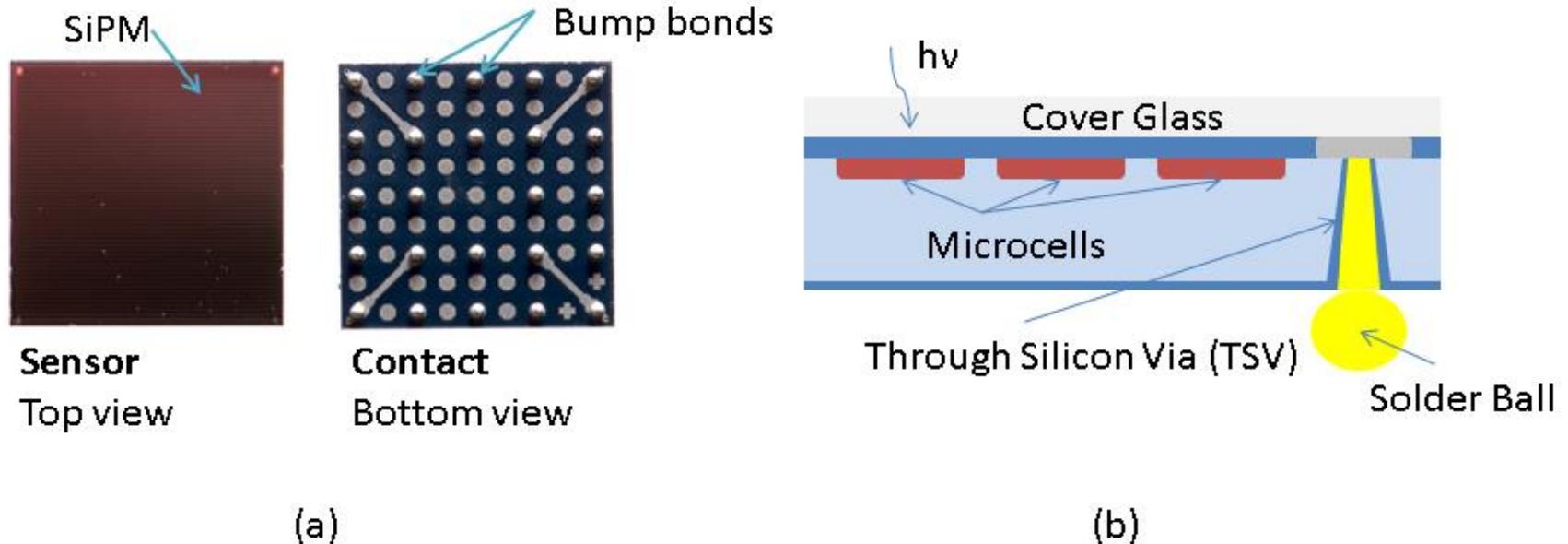
P on N technology provides the highest levels of Blue and UV photon sensitivity



Compatible with Fast Output (3-terminal) & Standard Output (2-terminal)

# Through Silicon Via (TSV) Overview

# SensL's Through Silicon Via (TSV)

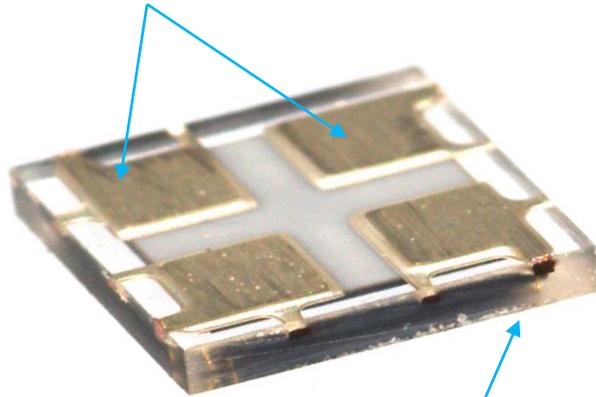


## Advantages of the SensL TSV package

- No ferrous metals and No wire bonds
- SensL's TSV process is a true wafer scale package
  - SiPM can be placed directly on PCB by customers with minimal deadspace

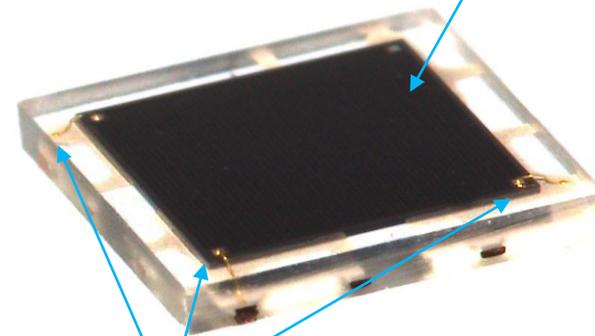
# Why TSV?

Micro Lead Frame



Clear Molded Epoxy

SiPM

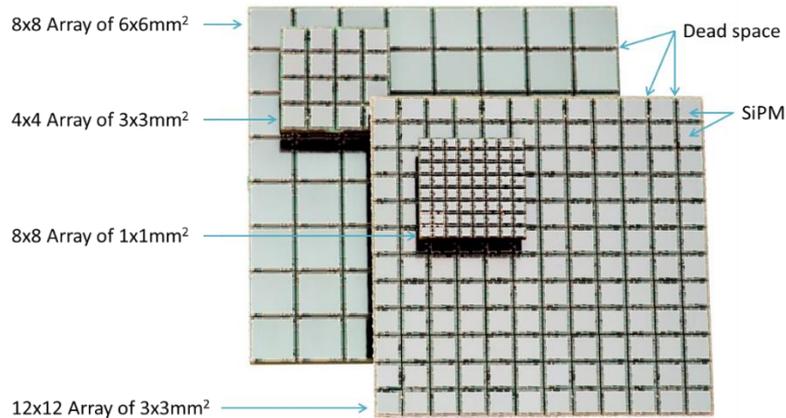


Wire Bonds

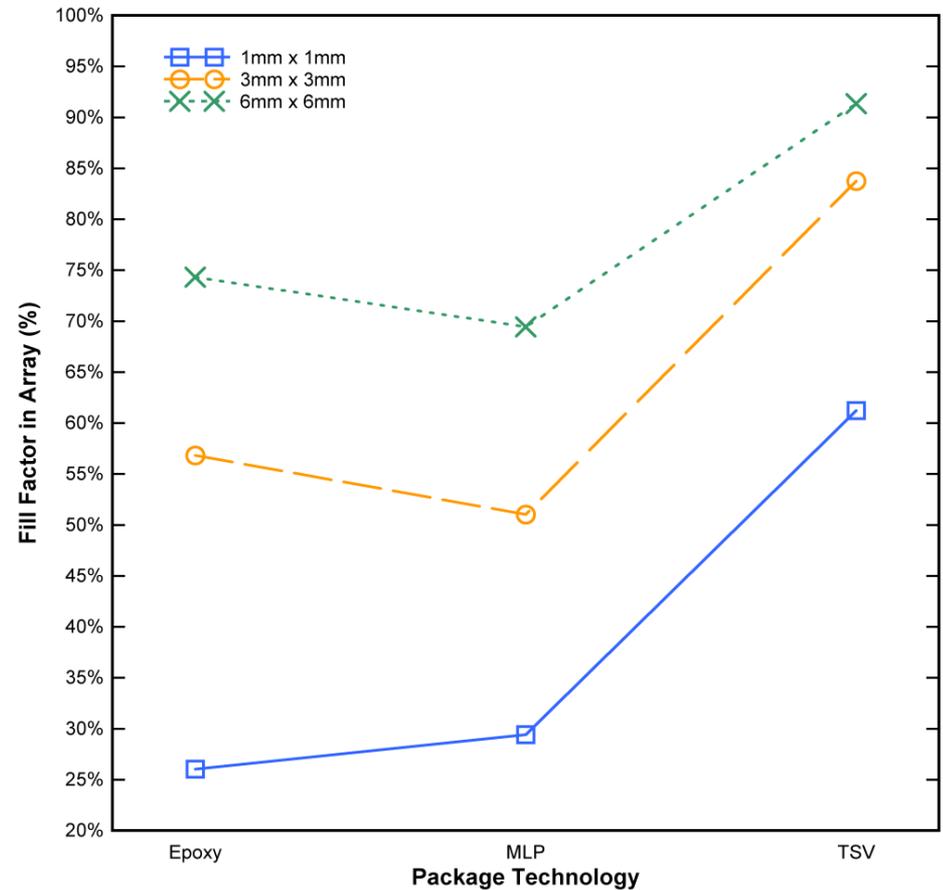
Die Size	Package Size	Active Area Fill Factor
1mm x 1mm	1.5mm x 1.8mm	37%
3mm x 3mm	4mm x 4mm	56%
6mm x 6mm	7mm x 7mm	73%

# TSV High Fill Factor

## Clear MLP SMT Arrays

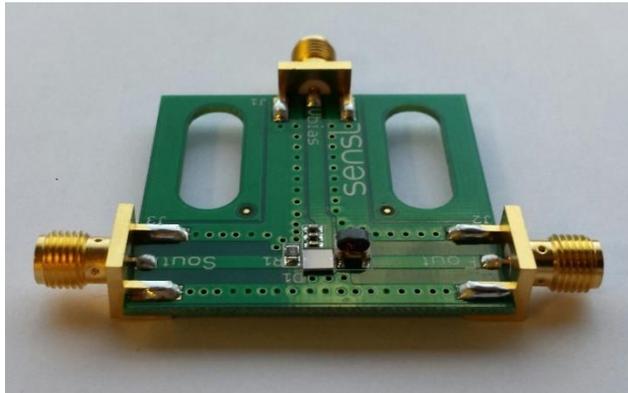


## TSV Array Fill Factor Comparison

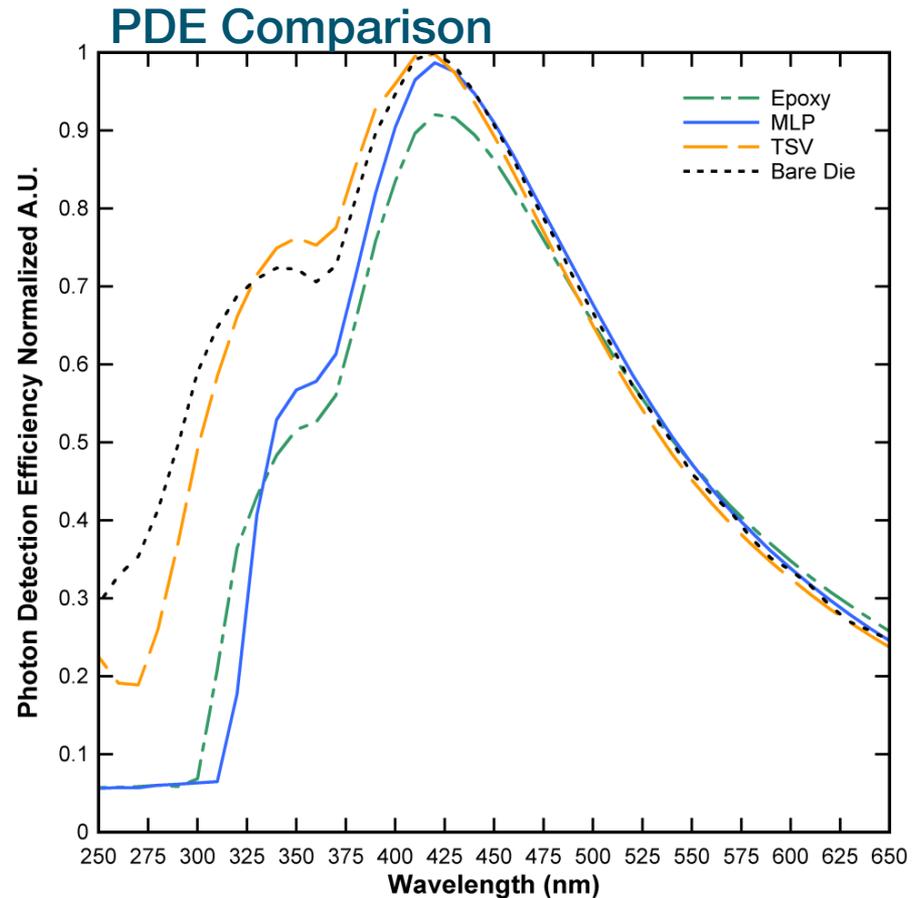


TSV Arrays provide >90% fill factor for 6mm x 6mm SiPM

# Photon Detection Efficiency (PDE)



TSV Test Board – SMA Output

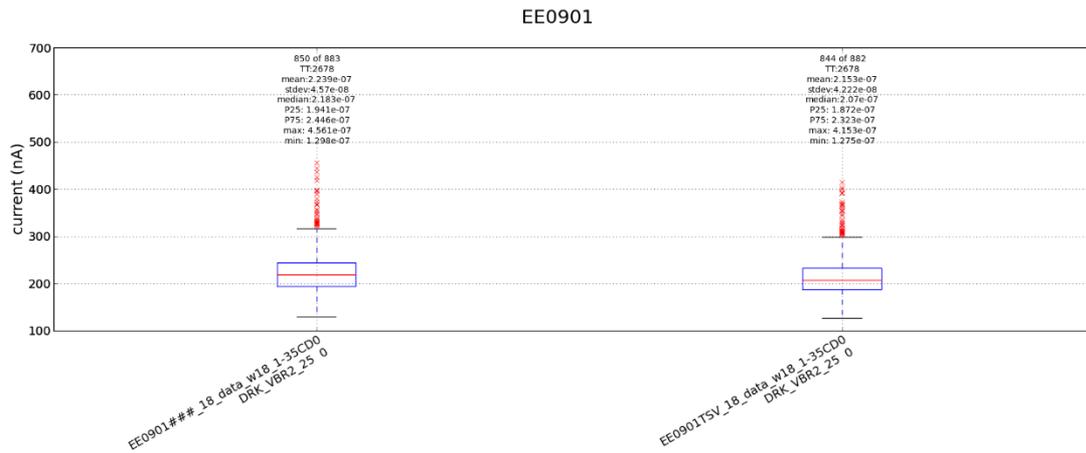
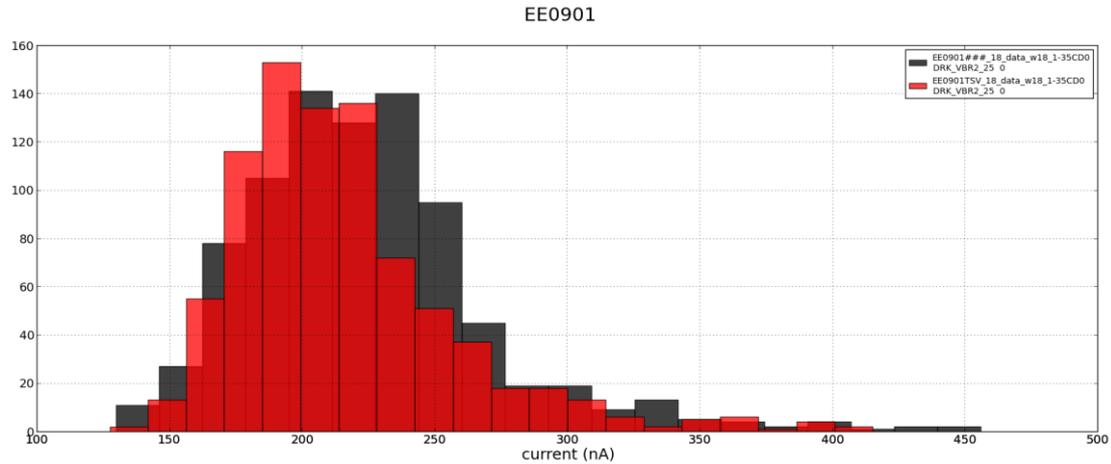


TSV glass has higher transmission compared to clear MLP

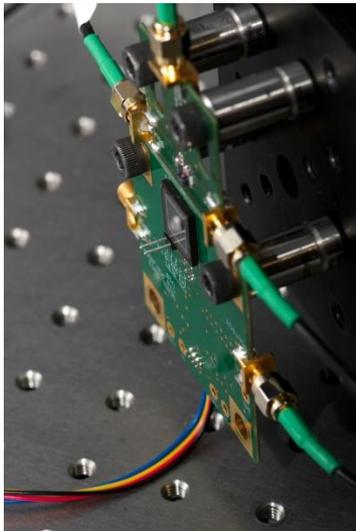
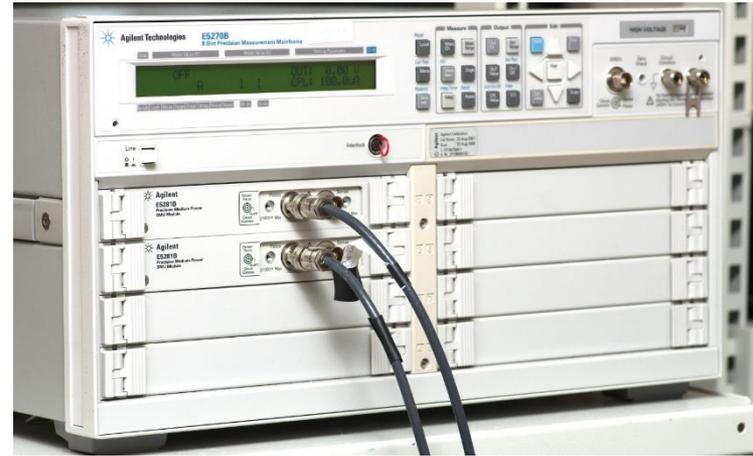
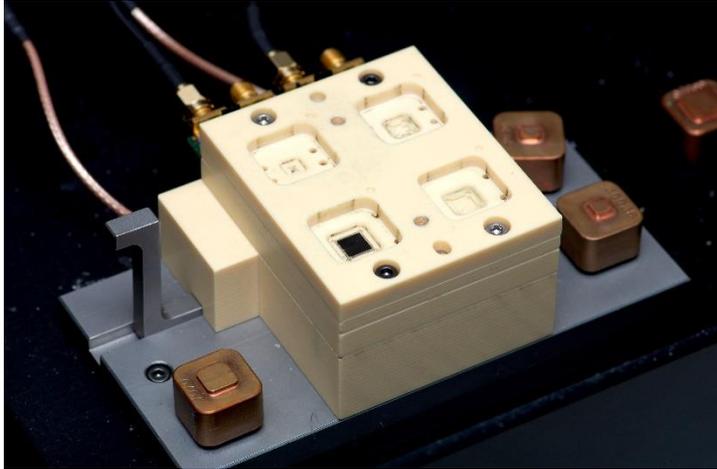
# TN1 Activities

TSV Development

# Initial Wafer Level Results

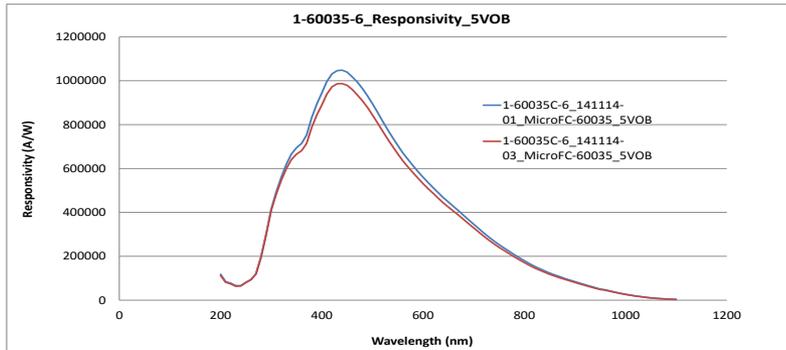


# Laboratory Test Capability Development

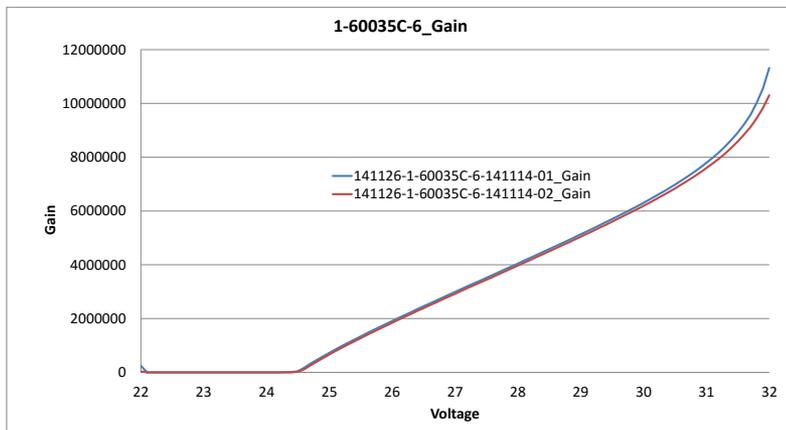


Die level and on PCB test infrastructure developed at SensL

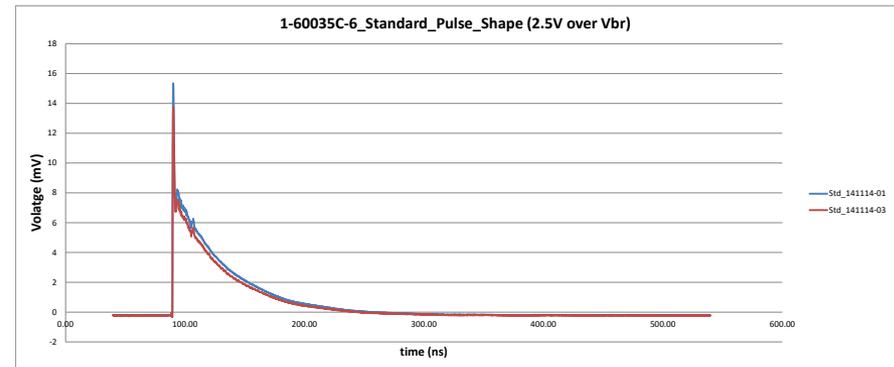
# Initial Laboratory Test Results



## Optical Responsivity



## Gain

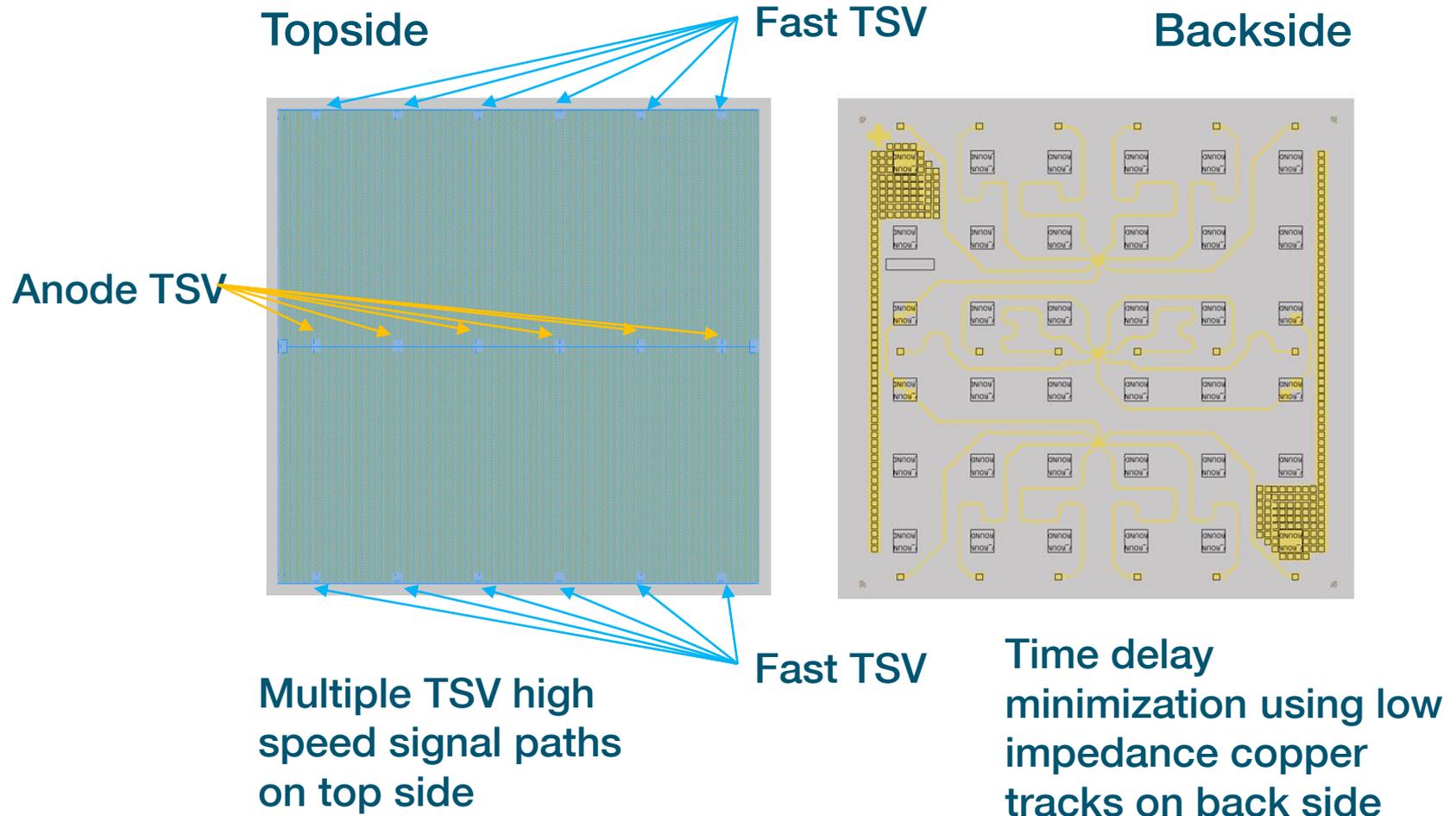


## Pulse Shape

# TN2 Activities

TSV Qualification & Reliability

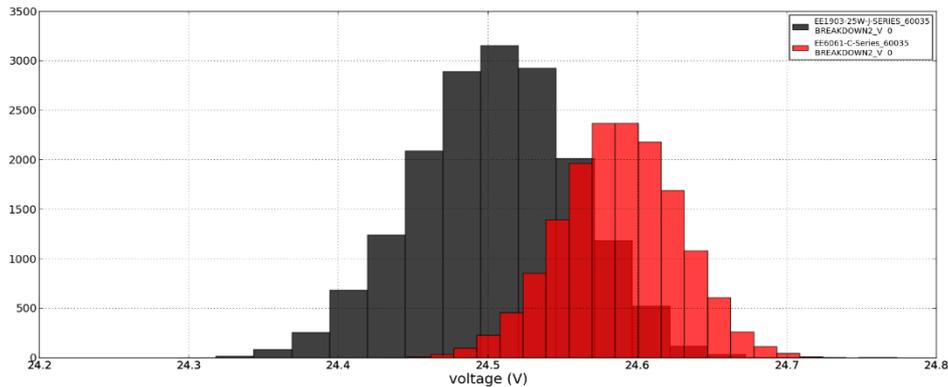
# Production Maskset



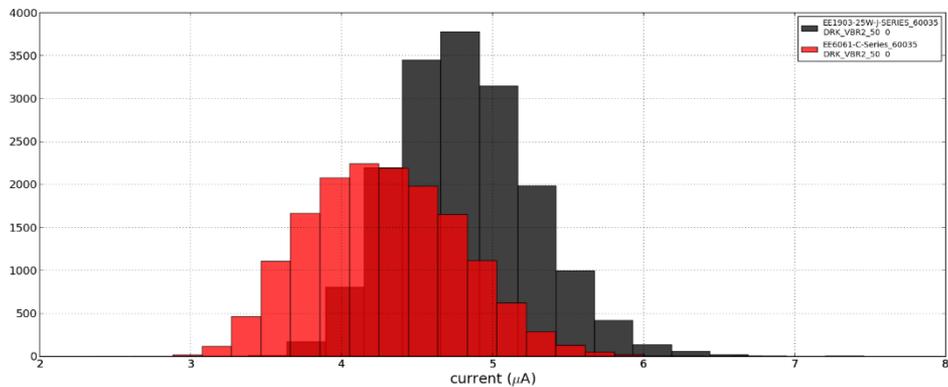
# Fabricated Sensors

## Wafer Level Results

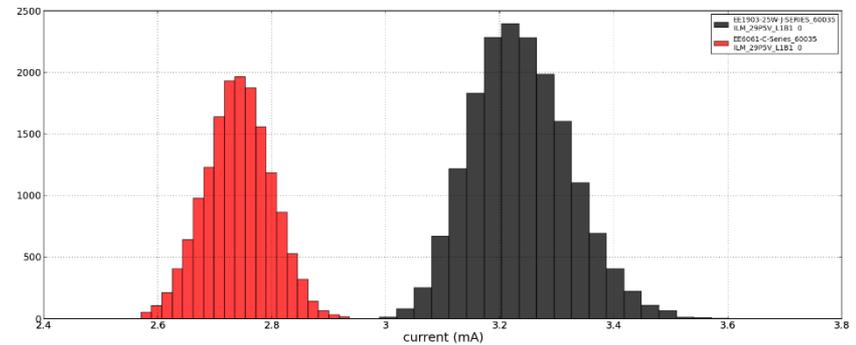
BREAKDOWN VOLTAGE



DARK CURRENT @ 5.0V OVERBIAS

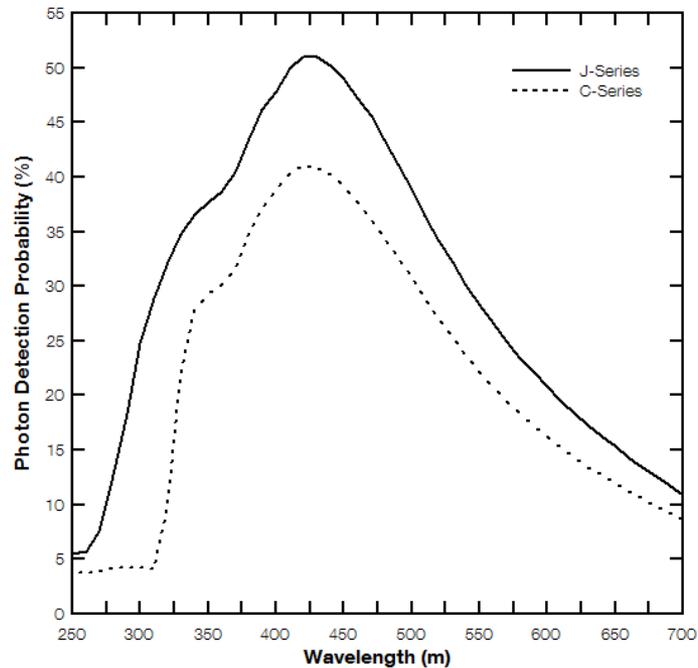


ILM\_29P5\_L1B1 C-SERIES vs J-SERIES

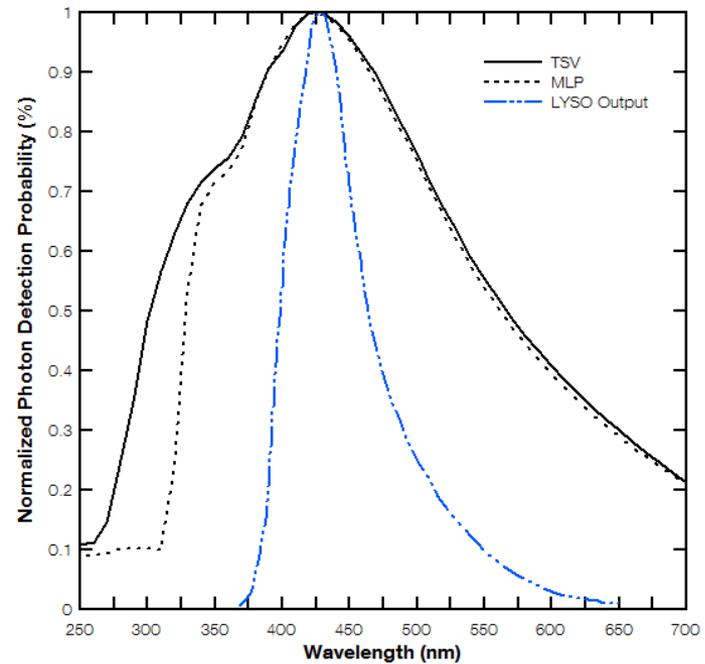


# Photon Detection Efficiency (PDE)

**PDE versus Wavelength**  
C-Series and J-Series at 5.0V Overvoltage



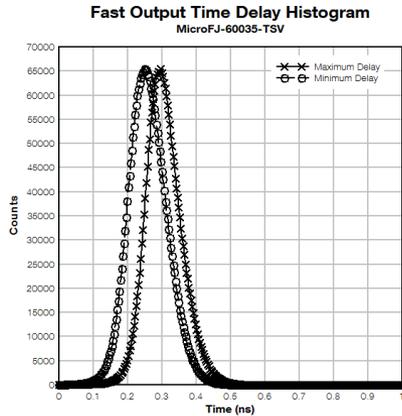
**PDE Package Comparison**  
LYSO, C-Series and J-Series at 5.0V Overvoltage



# Time Delay Measurements

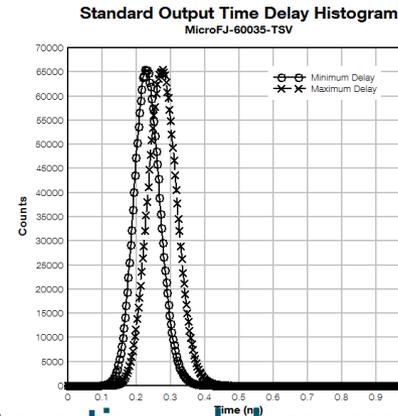
J-Series

## Fast Output



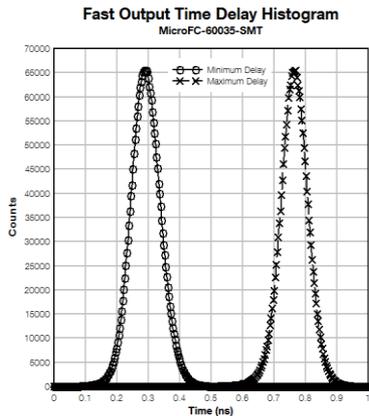
46 ps time delay spread

## Standard Output

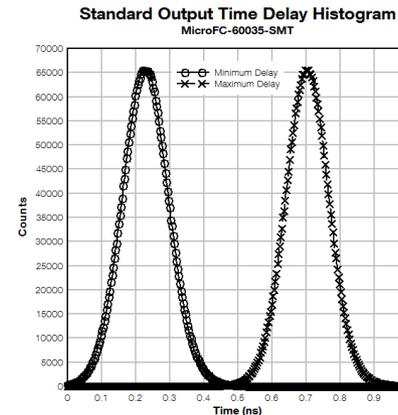


52 ps time delay spread

C-Series



476 ps time delay spread

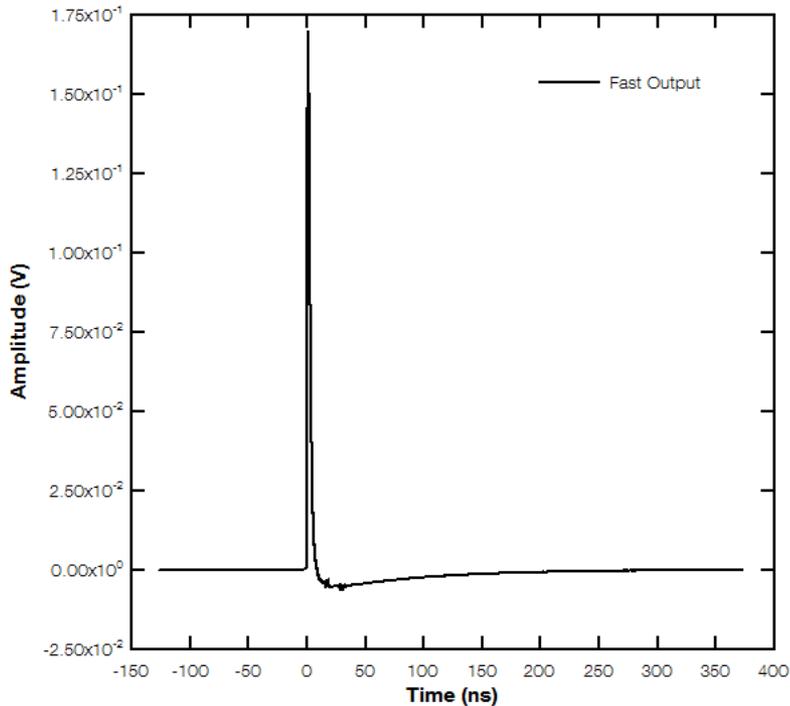


485 ps time delay spread

# Pulse Shapes

## Demonstrating Recovery Time Reduction

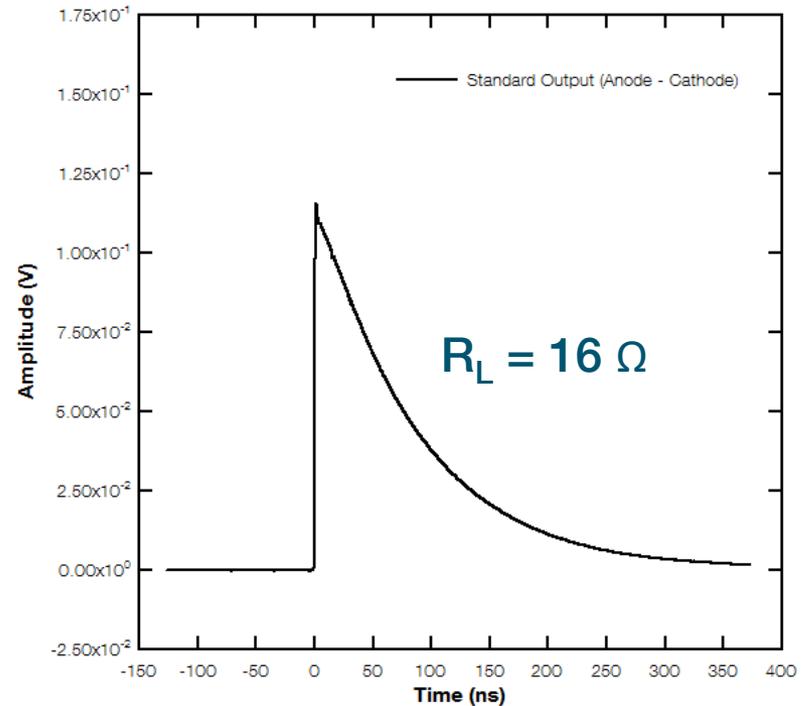
**Fast Output Pulse Shape**  
MicroFJ-60035-TSV



### Fast Terminal Performance

- Rise time 635 ps
- FWHM: 2.74 ns

**Standard Output Pulse Shape**  
MicroFJ-60035-TSV



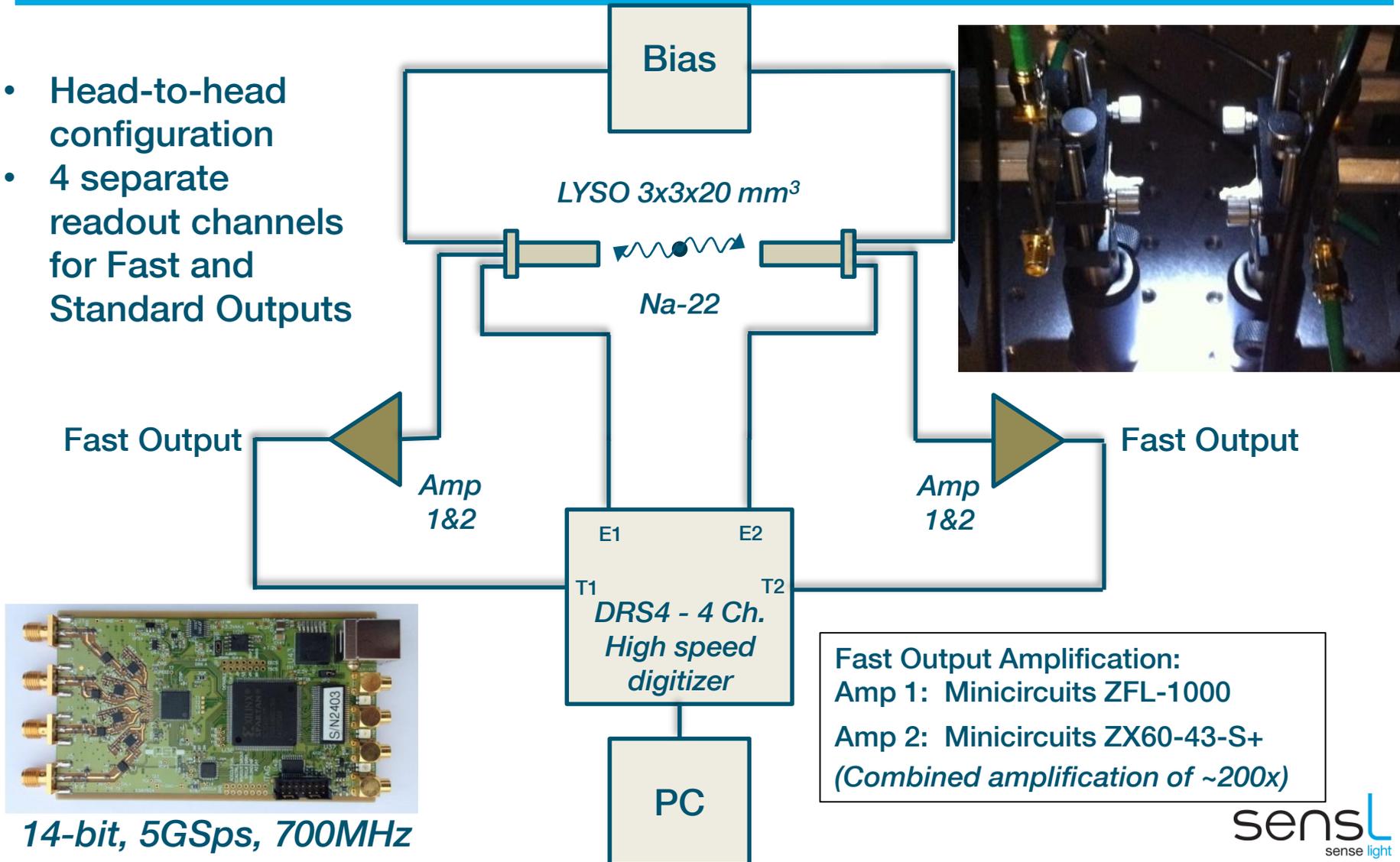
### Standard Terminal Performance:

- Rise time 706 ps
- Recovery Tau (1/e): 49 ns
- $1 \Omega$  External  $R_L$

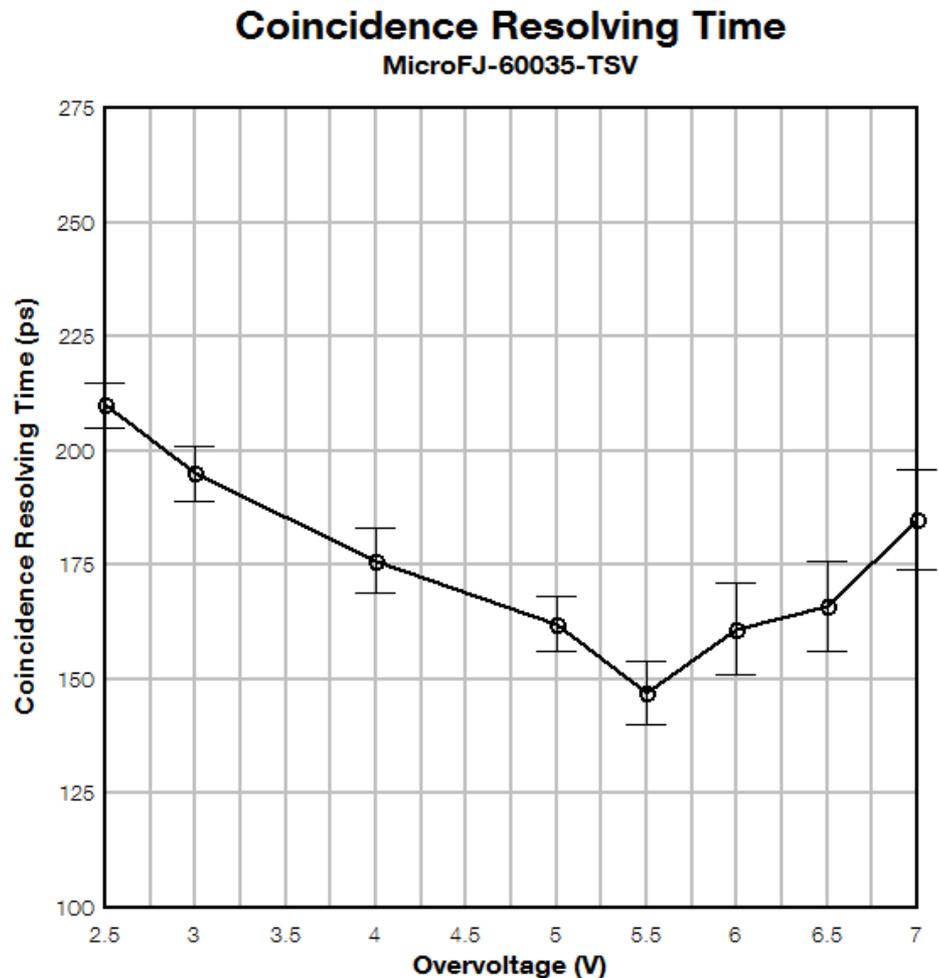
# Coincidence Resolving Time (CRT) Measurement Setup

## Measurement Setup

- Head-to-head configuration
- 4 separate readout channels for Fast and Standard Outputs



# Coincidence Resolving Time (CRT)



- Measurement conditions:
- 3 x 3 x 20 mm<sup>3</sup> LYSO:Ce
  - 6 mm SiPM
  - Head on test
  - Folded measurement using 2 SiPM

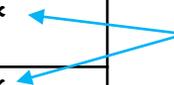
# Reliability Test Assessment Program

Test	Location	Ref.	Abbr.	Required Condition	Lot size	Status
High Temperature Operating life	Tyndall Institute	JESD22A 108	HTOL1	1000hr Ambient temperature = 125°C; bias>Vbr	3 lots / 77 units	at 500hr
High Temperature Operating life	Tyndall Institute	JESD22A 108	HTOL2	1000hr Ambient temperature = 85°C; bias>Vbr	1 lot / 77 units	at 500hr
Human Body Model ESD	EAG	JESD22-A114	ESD-HBM	Ta = 25°C	3 units	DONE
Moisture Level Definition	Tyndall Institute	J-STD-020	MLD	MSL treatment to levels set out in the standard; followed by solder simulation according to the specified solder conditions		Passed level 3
Preconditioning	Tyndall Institute	JESD22-A113	PRE	MSL3; 3 times reflow; peak body temperature 260°C	Applied to all parts prior to temperature cycling and thermal UHAST	DONE
Unbiased Highly Accelerated Stress	Maser	JESD22-A118	UHAST	110°C, 85%RH	3 Lots / 25 units	DONE
Temperature Cycling	Tyndall Institute	JESD22-A104	TC	500 cycles; -40C to 85C, 15 sec transition, 15 min dwell time	3 Lots / 25 units	DONE
High Temperature Storage Test	Tyndall Institute	JESD22-A103	HTS	504HRS HTS@125°C	3 Lots / 25 units	DONE
Characterisation	SensL	Functional Specification	CHAR	See Functional Specification	3 lots/ 10 units	DONE

# Characterisation Summary

Parameter	Abbr.	Unit	Notes	Target Specification	Specification Met
Breakdown voltage	Vbr	V	21°C	24.5	✓
Fill Factor	F	%		90%	✓
Photo-detection Efficiency	PDE	%	21°C , at max $\lambda$ ; Vbr + 2.5V	31%	✓
Gain	G		21°C , at Vbr + 2.5V	$3 \times 10^6$	✓
Peak sensitivity wavelength	$\lambda_p$	nm	21°C, at Vbr + 2.5V	420	✓
Dark current	I <sub>dark</sub>	$\mu$ A	21°C, at Vbr + 2.5V	3.2	✓
Signal rise time: fast mode	t <sub>ff</sub>	ns	21°C, 10 to 90%	0.6	x
Pules width: fast mode	PW	ns	21°C, 90 to 10%	1.5	x
Microcell recovery time: standard mode	t <sub>re</sub>	ns	21°C, 90 to 10%	180	✓
Temp dependence of Vbr	Vbr(T)	mV/°C	Various temperatures	21.5	✓
Optical cross talk probability	XT	%	21°C, at Vbr + 2.5V	10	✓

Modified Specification Acceptable to customers

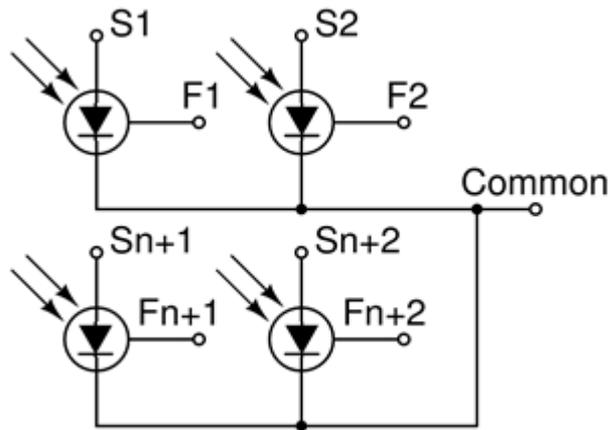


# TN3 Activity

Array Development

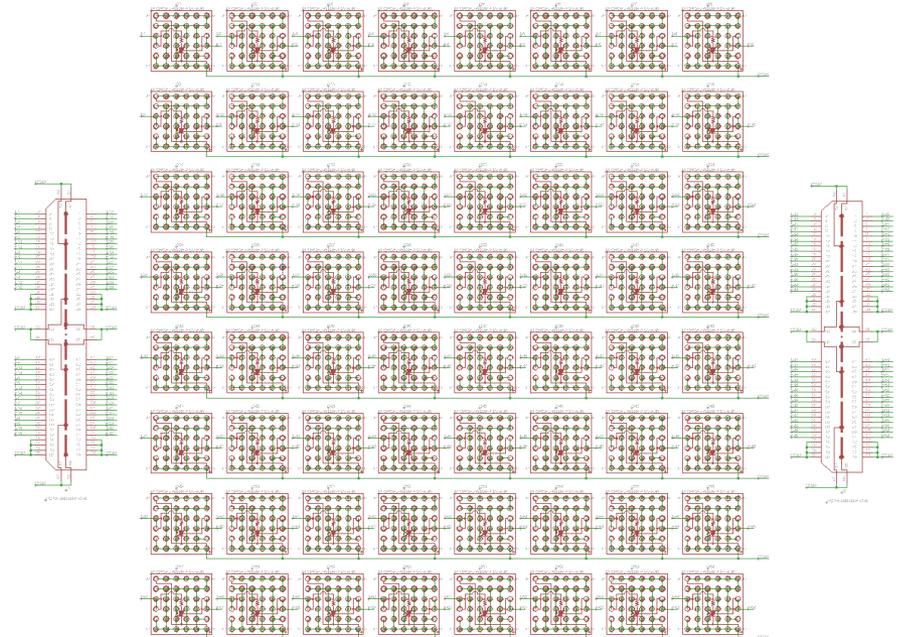
# 8x8 Array Development

## Internal Wiring Summary



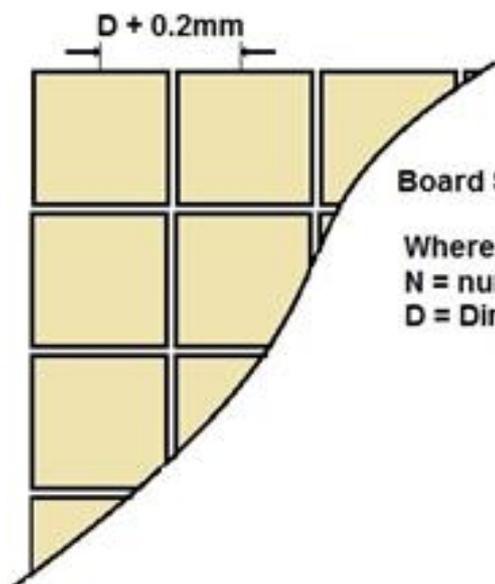
- 64x Fast Outputs
- 64 x Standard Anode I/O
- 48 x pins connected to the common Cathode I/O

## Schematic of 8x8 Array



# Design Rules and CAD of 8x8 Array

## SiPM Spacing Design Rule



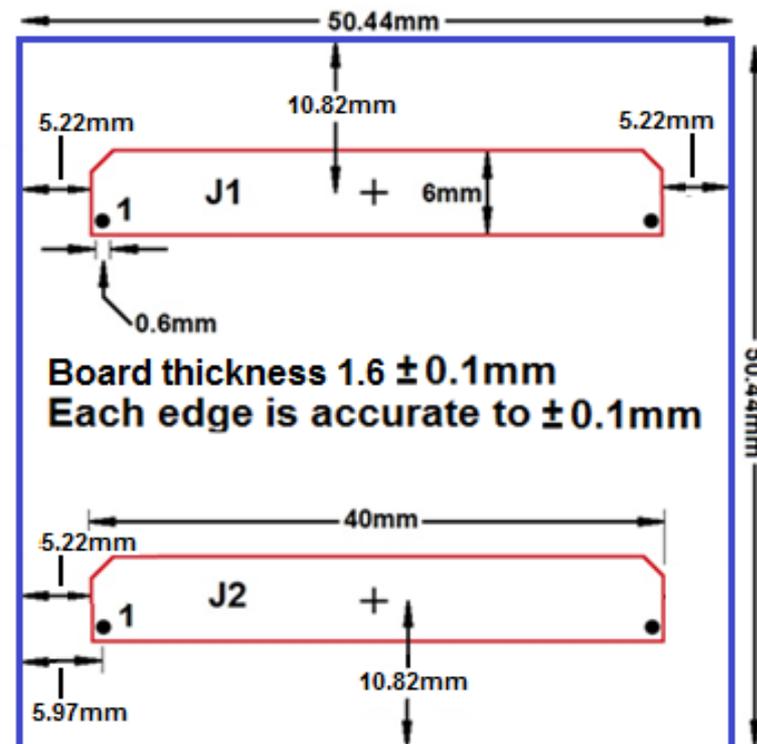
$$\text{Board Size} = (N \times D) + ((N-1) \times 0.2\text{mm})$$

Where:

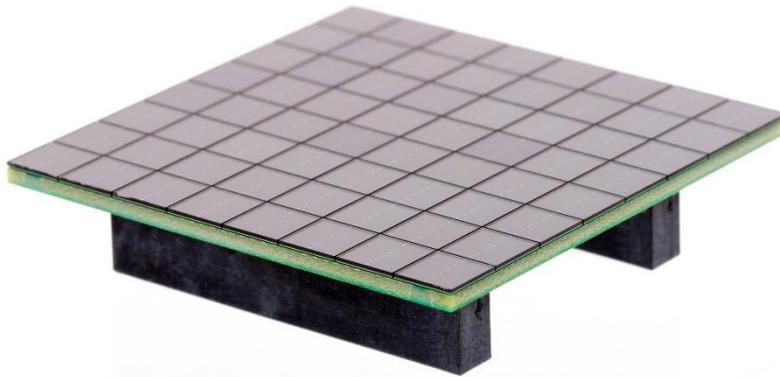
N = number of devices per side

D = Dimension of device

## CAD of 8x8 Array

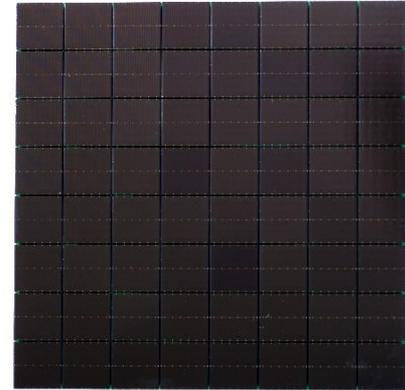


# 8x8 Array Images

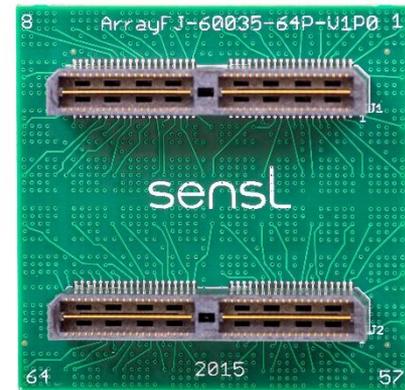


Side View

Top Side View



Back Side View



# Conclusions

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- A large area SiPM in a TSV process capability has been developed
- A large area SiPM in a TSV packaged product has been demonstrated
  - Reliability and qualification assessment has been carried out
- An 8x8 array of the large area SiPM has been developed
  - Reliability and qualification assessment has been carried out
- Customer validation has been performed with over 41 customers

# Final Slide